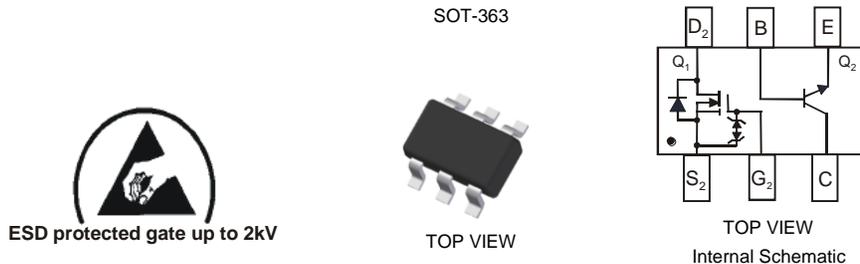


## Features

- N-Channel MOSFET and NPN Transistor in One Package
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected MOSFET Gate up to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

## Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 Lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.006 grams (approximate)



## Maximum Ratings – MOSFET, Q1 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 4)	I <sub>D</sub>	160	mA
Pulsed Drain Current (Note 4)	I <sub>DM</sub>	560	mA

## Maximum Ratings - NPN Transistor, Q2 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	45	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	100	mA

## Thermal Characteristics, Total Device (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 4)	P <sub>D</sub>	250	mW
Thermal Resistance, Junction to Ambient (Note 4)	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Incorporated's suggested pad layout document, which can be found on our website at <http://www.diodes.com/package-outlines.html>.

**Electrical Characteristics - MOSFET** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 1)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	1.0 5.0	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 1)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.7	0.8	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	3.1	4	Ω	V <sub>GS</sub> = 4V, I <sub>D</sub> = 100mA
		—	4	5		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 80mA
Forward Transconductance	g <sub>FS</sub>	180	—	—	ms	V <sub>DS</sub> = 10V, I <sub>D</sub> = 100mA, f = 1.0kHz
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	25	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	5	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.1	—	pF	

**Electrical Characteristics - NPN Transistor** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 5)	V <sub>(BR)CBO</sub>	50	—	—	V	I <sub>C</sub> = 10μA, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage (Note 5)	V <sub>(BR)CEO</sub>	45	—	—	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage (Note 5)	V <sub>(BR)EBO</sub>	6	—	—	V	I <sub>E</sub> = 1μA, I <sub>C</sub> = 0
DC Current Gain (Note 5)	h <sub>FE</sub>	200	290	450	—	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA
Collector-Emitter Saturation Voltage (Note 5)	V <sub>CE(SAT)</sub>	—	—	100 300	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage (Note 5)	V <sub>BE(SAT)</sub>	—	700 900	—	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Voltage (Note 5)	V <sub>BE</sub>	580 —	660 —	700 770	mV	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA
Collector Cut-Off Current (Note 5)	I <sub>CBO</sub>	—	—	15 5.0	nA μA	V <sub>CB</sub> = 30V V <sub>CB</sub> = 30V, T <sub>A</sub> = +150°C
Collector-Emitter Cut-Off Current (Note 5)	I <sub>CES</sub>	—	—	-100	nA	V <sub>CE</sub> = -45V
Gain Bandwidth Product	f <sub>T</sub>	100	—	—	MHz	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA, f = 100MHz
Output Capacitance	C <sub>OBO</sub>	—	—	4.5	pF	V <sub>CB</sub> = 10V, f = 1.0MHz
Noise Figure	NF	—	—	10	dB	V <sub>CE</sub> = 5V, R <sub>S</sub> = 2.0kΩ, f = 1.0kHz, BW = 200Hz

Note: 5. Short duration pulse test used to minimize self-heating effect.

**MOSFET**

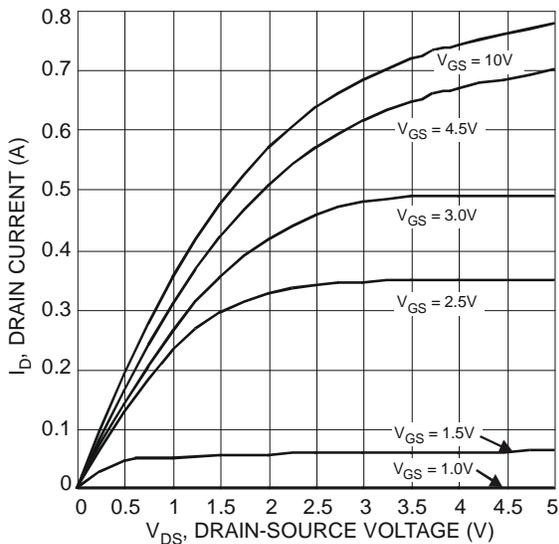


Fig. 1 Typical Output Characteristics

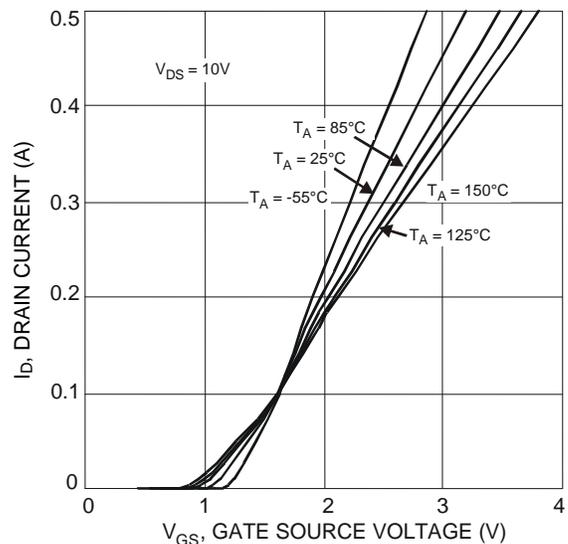


Fig. 2 Typical Transfer Characteristics

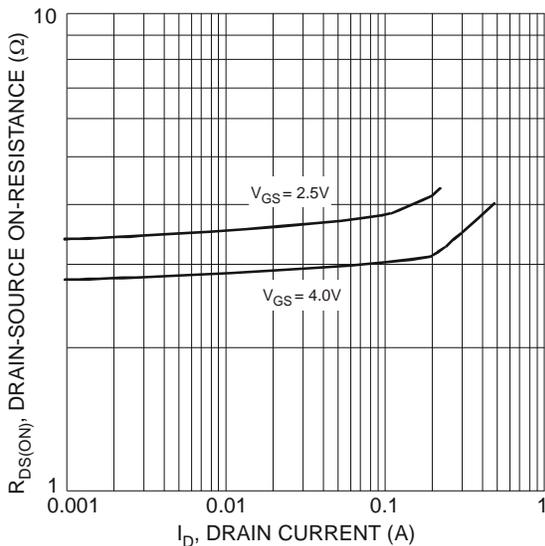


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

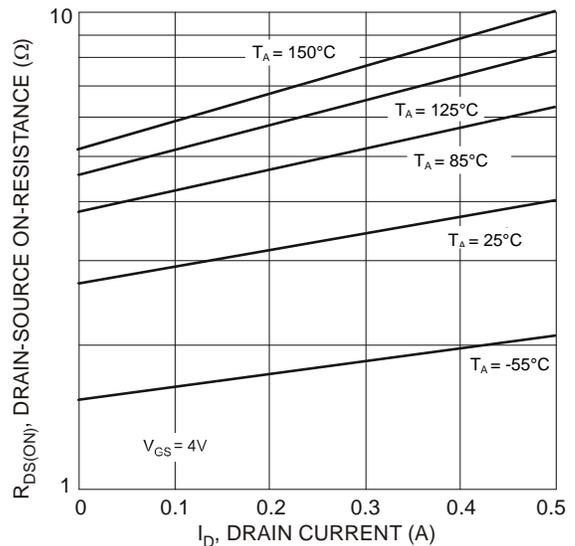


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

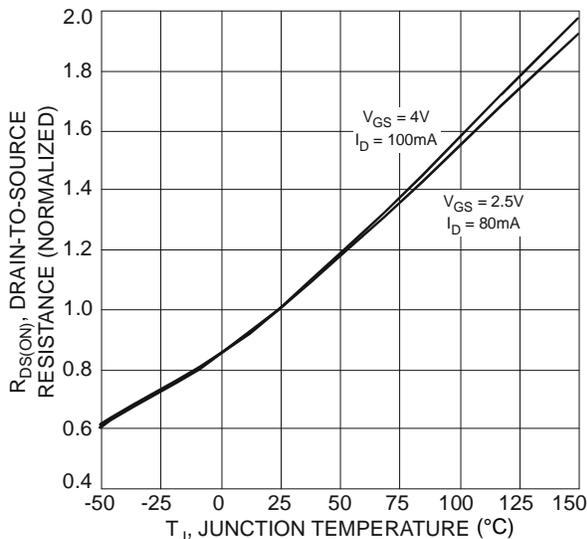


Fig. 5 On-Resistance Variation with Temperature

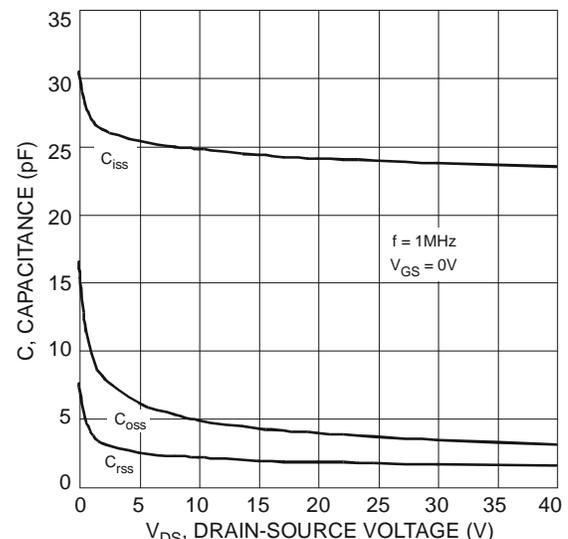


Fig. 6 Typical Capacitance

**MOSFET (continued)**

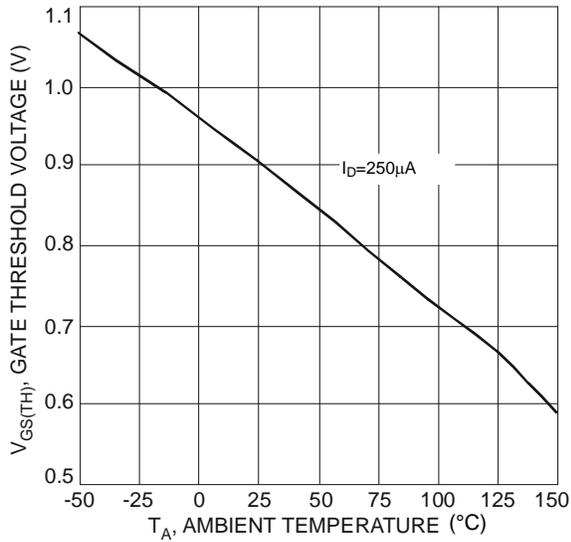


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

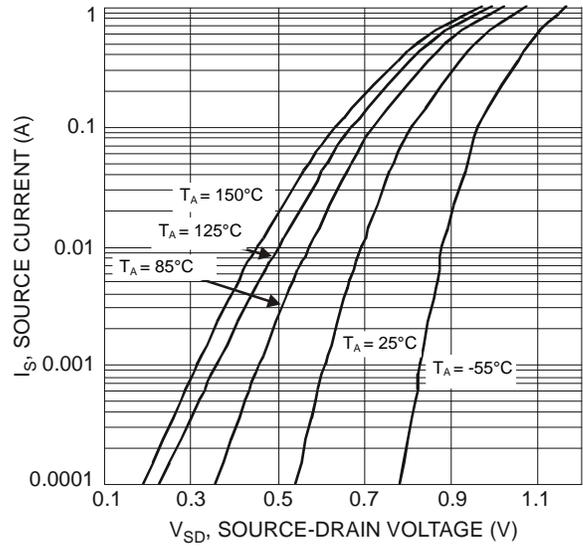


Fig. 8 Diode Forward Voltage vs. Current

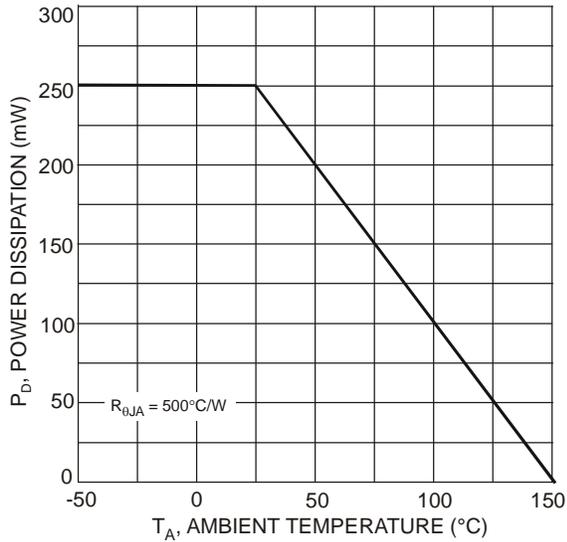


Fig. 9 Derating Curve - Total Package Power Dissipation

**NPN Transistor**

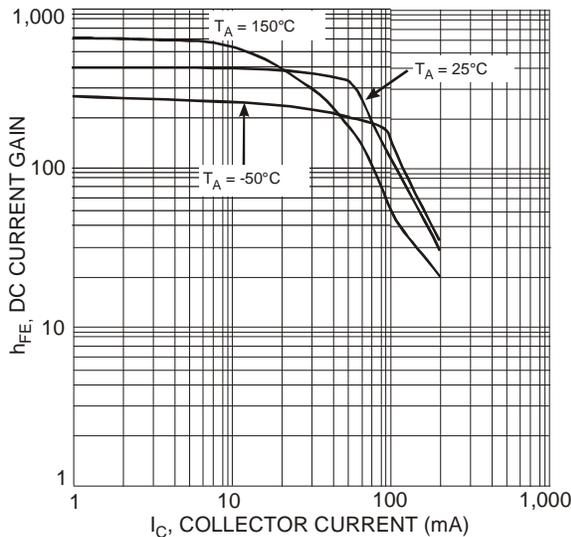


Fig. 10 Typical DC Current Gain vs. Collector Current

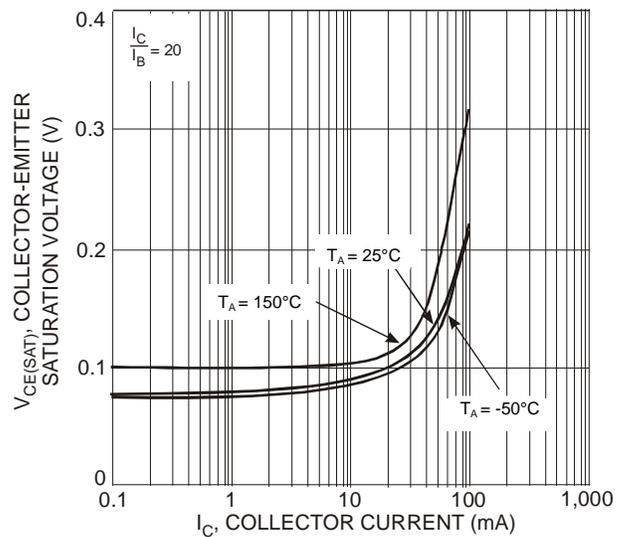


Fig. 11 Typical Collector-Emitter Saturation Voltage vs. Collector Current

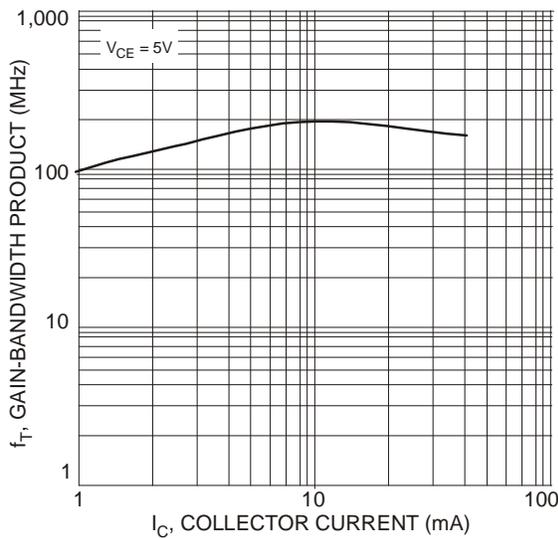


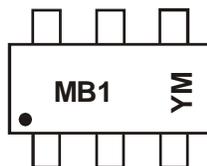
Fig. 12 Typical Gain-Bandwidth Product vs. Collector Current

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DMB53D0UDW-7	SOT-363	3000/Tape & Reel

Note: 6. For packaging details, go to our website at <https://www.diodes.com/assets/Packaging-Support-Docs/Ap02007.pdf>.

**Marking Information**



MB1 = Marking Code  
YM = Date Code Marking  
Y = Year (ex: V = 2008)  
M = Month (ex: 9 = September)

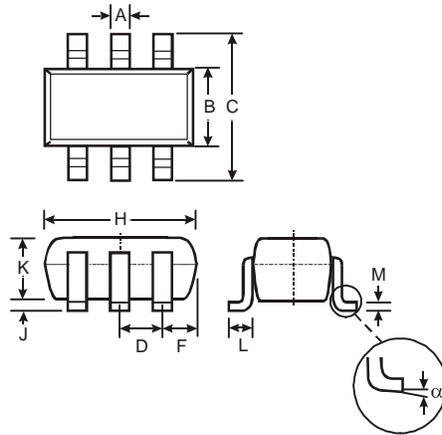
Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**

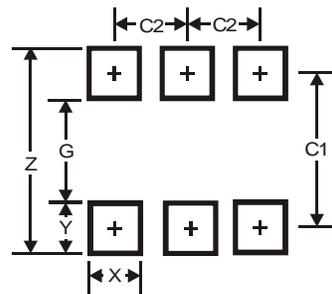
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
<b>All Dimensions in mm</b>		

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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